

Influence of Deformation Potential Scattering on Impact Ionization in Ultra-Wide Bandgap Materials

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ULTRA Semiconductors



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- sp³ bonded carbon
- C-6e
- Diamond Cubic a = 3.57 Å

Why ULTRA materials for power electronics: Large bandgap gives high breakdown voltage (limited by avalanche breakdown) and hence high figure of merit:

$$FOM = \frac{V_B^2}{R_{on,sp}}$$



G. L. Doll, J. A. Sell, C. A. Taylor II, and R. Clarke, Phys. Rev. B, 43, 6816 (1991).







M. Saraniti and S.M. Goodnick, IEEE TED, 47, 1909 (2000)

Electronic Structure

- Density Functional Theory (DFT) in Quantum Espresso (QE) is used to calculate the electronic band structure based on the ground-state charge density, computed using pseudopotential inputs.
- BerkeleyGW uses the DFT result from QE as a starting point, and calculates excited states (i.e. conduction band energies) more accurately using Green's functions.
- DFT typically under-estimates band-gaps, while GW produces more accurate estimations.
 - GW band-gap estimations get more accurate with selfconsistent iterative solutions.
 - The DFT conduction bands on the right have been shifted upward to match the GW band-gap.







Phonon Dispersion

- Phonon frequencies are computed using Density Functional Perturbation Theory (DFPT) in Quantum Espresso
- The choice of pseudopotential (PP) input file has a large effect on the resulting dispersion with the commonly used lattice constant in diamond
- A relaxed lattice constant (Pavone et al.) converges phonon dispersions from different PP's together in diamond
- Ultra-soft pseudopotentials (not shown) can reproduce the experimental points more accurately, but aren't compatible with GW algorithms





Pavone, P., et al. *Physical Review B* 48.5 (1993): 3156. Guzman, Erick, et al. *ACS Applied Materials & Interfaces* 14.37 (2022): 42223-42231



Impact Ionization Scattering Rate

Two approaches to calculating impact ionization transition rate:

- 1. Screened Coulomb interaction 2 particles, internal
- 2. Self-energy from GW (Schilfgaarde et al., Usaka et al.)

Impact ionization rate from screened Coulomb interaction: $\frac{1}{\tau} = \frac{2\pi}{\hbar} \frac{V^3}{(2\pi)^9} \sum_{n_1, n_2, n_{2'}} \iiint d\mathbf{k}_1, d\mathbf{k}_2 d\mathbf{k}_2, \checkmark$ $\times |M(n_{1'}, \mathbf{k}_{1'}, n_{2'}, \mathbf{k}_{2'}; n_1, \mathbf{k}_1, n_2, \mathbf{k}_2)|^2$ $\times \delta \big(E(\boldsymbol{k}_{1\prime}) + E(\boldsymbol{k}_{2\prime}) - E(\boldsymbol{k}_{1}) - E(\boldsymbol{k}_{2}) \big) \blacktriangleleft$ $|M|^2 = |M_D|^2 + |M_E|^2 - (M_D^* M_E + M_D M_E^*)/2$ $M_{D} = \sum_{\boldsymbol{G}_{1}, \boldsymbol{G}_{2}, \boldsymbol{G}_{1'}, \boldsymbol{G}_{2'}} a_{n_{1'}, \boldsymbol{k}_{1'}}^{*} (\boldsymbol{G}_{1'}) a_{n_{2'}, \boldsymbol{k}_{2'}}^{*} (\boldsymbol{G}_{2'}) \\ \times a_{n_{1}, \boldsymbol{k}_{1}} (\boldsymbol{G}_{1}) a_{n_{2}, \boldsymbol{k}_{2}} (\boldsymbol{G}_{2}) \frac{e^{2}}{4\pi\epsilon(q_{D}, \omega_{D})q_{D}^{2}}$ $\times \delta(\mathbf{k}_{1\prime} + \mathbf{G}_{1\prime} + \mathbf{k}_{2\prime} + \mathbf{G}_{2\prime} - \mathbf{k}_1 - \mathbf{G}_1 - \mathbf{k}_2 - \mathbf{G}_2)$



Integration across the hot carrier final state k_1 , and cool carrier initial and final states k_2 and k_2 .

Delta function constraints across energy and momentum eliminate one of the three integrals.

Exchange matrix element M_E is found by switching states 1' and 2'.

Sum across all four states' reciprocal lattice vectors requires full knowledge of the band structure and wave-functions. (only valid for plane wave expansion)

Watanabe, Tomokatsu, et al. Journal of applied physics 95.9 (2004): 4866-4874. Kamakura, Y., et al. 2016 International Conference on Simulation of Semiconductor Processes and Devices (SISPAD). IEEE, 2016.



Full-Band Lindhard Dielectric Function

- Full-band and energy-transfer dependence are needed for the dielectric function.
- Static approximation ($\omega = 0$) ceases to be valid when energy transfers on the order of 5-10 eV are taking place to ionize cool carriers across ultra-wide bandgaps.

Full-band-dependent Lindhard dielectric function:

$$\varepsilon_{1}(\boldsymbol{q},\omega) = \varepsilon_{0} + \frac{e^{2}}{\Omega q^{2}} \sum_{\Delta \boldsymbol{k},c,\nu} |\langle \boldsymbol{k} + \boldsymbol{q},c | \boldsymbol{k},\nu \rangle|^{2} (\Delta \boldsymbol{k})^{3} \\ \times \left\{ \frac{1}{E_{c}(\boldsymbol{k}+\boldsymbol{q})-E_{\nu}(\boldsymbol{k})-\hbar\omega} + \frac{1}{E_{c}(\boldsymbol{k}+\boldsymbol{q})-E_{\nu}(\boldsymbol{k})+\hbar\omega} \right\}$$

$$\varepsilon_2(\boldsymbol{q},\omega) = \frac{\pi e^2}{\Omega q^2} \sum_{\Delta \boldsymbol{k},c,\nu} |\langle \boldsymbol{k} + \boldsymbol{q},c | \boldsymbol{k},\nu \rangle|^2 (\Delta \boldsymbol{k})^3 \delta(E_c(\boldsymbol{k} + \boldsymbol{q}) - E_v(\boldsymbol{k}) - \hbar \omega)$$





Dielectric function of diamond along the [100] direction for various values of $|\vec{q}|$



GW-Derived Impact Ionization Scattering Rat

- The CMC code was modified to import BerkeleyGW calculated eigenvalues and wavefunctions
- Using the GW electronic structure as input, the anisotropic impact ionization rate is calculated directly from GW.
- Also possible to directly calculate the impact ionization rate from the self-energy in GW (van Schilfgaarde *Physical Review B 81*, 125201 (2010))





Deformation Potential Scattering



The deformation potential scattering rate from point \vec{k} in band v to a region $\Omega_{\vec{k'}}$ centered around the point $\vec{k'}$ in band ν' for phonon mode η is calculated using Fermi's Golden Rule:

$$\tau^{-1}\left(\vec{k},\Omega_{\vec{k'}},\nu,\nu',\eta\right)$$
$$=\frac{\pi}{\rho\omega_{\eta\vec{q}}}\left|\Delta^{(\eta)}\left(\nu',\vec{k},\vec{q},\nu\right)\right|^{2}\left|I\left(\nu,\nu',\vec{k},\vec{k'}\right)\right|^{2}D_{\nu'}(\epsilon',\Omega_{\vec{k'}})\left(N_{\eta\vec{q}}+\frac{1}{2}\mp\frac{1}{2}\right)\right|$$

Scattering Rate $1/\tau$ (s⁻¹) $\Delta^{(\eta)}(\nu', \vec{k}, \vec{q}, \nu)$ is the deformation potential for phonon mode η between the initial carrier state with wave-vector \vec{k} and band number ν and the final carrie. state with $\vec{k'} = \vec{k} \pm \vec{q}$ and ν' . This has heretofore typically been assumed isotropic and approximated with a constant value for all initial and final states, so that the deformation potential reduces as $\Delta^{(\eta)}(\nu', \vec{k}, \vec{q}, \nu) \rightarrow \Delta_{const}$.

Electron-Phonon Scattering Rates Computed From Constant Deformation Potentials





Impact Ionization Coefficients





- Full-Band Monte Carlo simulations with varying E-field strength along the [100] direction
- Impact ionization coefficients are calculated for each E-field using

$$\alpha_i(E) = \frac{1}{N\overline{\nu}_i(E)} \frac{dn_i(E)}{dt}$$

• The results are fitted to Chynoweth's law:

$$\alpha_{n,p} = A_{n,p} exp\left(-\frac{B_{n,p}}{|E|}\right)$$





- Large differences between the deformation potentials leads to large discrepancies between ionization coefficient results.
- This motivated us to study EPW (Electron-Phonon with Wannier) and first-principles calculations of deformation potentials.



Ab Initio Electron-Phonon Interactions

• The deformation potentials can be obtained from the electron-phonon interaction matrix elements, which are calculated *ab initio* using the EPW (Electron-Phonon using Wannier functions) code suite in Quantum Espresso using

$$g_{\vec{q}\nu}(\vec{k},\nu,\nu') = \left(\frac{\hbar}{2m_0\omega_{\vec{q}\eta}}\right)^{1/2} \left\langle \psi_{\nu,\vec{k}} \left| \frac{dV_{SCF}}{d\hat{u}_{\vec{q}\eta}} \cdot \hat{\epsilon}_{\vec{q}\eta} \right| \psi_{\nu',\vec{k}+\vec{q}} \right\rangle$$

• After extracting the deformation potentials for each \vec{k} to $\vec{k'}$ transition from the EPW code output, we can import the deformation potentials into our CMC code to calculate the deformation potential scattering rates.



Electron-Phonon Scattering Rates From Constant vs Wave Vector-Dependent Deformation Potentials





Ionization Coefficients in Diamond

- The deformation scattering transition rates obtained from EPW are used with the *ab initio* impact ionization transition rates in bulk diamond full-band Cellular Monte Carlo simulations with varying electric field strengths to obtain the field-dependent ionization rates.
- As observed on the right, importing the *ab initio* deformation potentials from EPW increases the measured ionization rate for both electrons and holes.
- Ionization rates obtained from DFT electronic structure are significantly different from the GW rates, demonstrating that finer band structure features have a notable effect.





Conclusion



- Simulated ionization coefficients are highly dependent on the choice of deformation potential inputs.
- Deformation potentials from *ab initio* methods (EPW) increase the resulting ionization coefficients.
- The choices of electronic and phonon band structure inputs are also important.
- This methodology will be extended to other UWBG materials, including cubic BN and AlN alloys (AlGaN, BAIN).



Velocity Field





